

DS1557 4Meg, Nonvolatile, Y2K-Compliant Timekeeping RAM

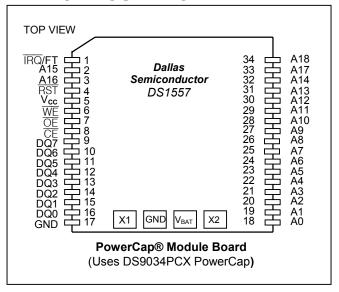
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FEATURES

- Integrated NV SRAM, Real-Time Clock (RTC), Crystal, Power-Fail Control Circuit, and Lithium Energy Source
- Clock Registers are Accessed Identically to the Static RAM; These Registers Reside in the 16 Top RAM Locations
- Century Byte Register (i.e., Y2K Compliant)
- Totally Nonvolatile with Over 10 Years of Operation in the Absence of Power
- Precision Power-On Reset
- Programmable Watchdog Timer and RTC Alarm
- BCD-Coded Year, Month, Date, Day, Hours, Minutes, and Seconds with Automatic Leap Year Compensation Valid Up to the Year 2100
- Battery Voltage-Level Indicator Flag
- Power-Fail Write Protection Allows for ±10% V_{CC} Power-Supply Tolerance
- Lithium Energy Source is Electrically Disconnected to Retain Freshness Until Power is Applied for the First Time
- Also Available in Industrial Temperature Range: -40° C to $+85^{\circ}$ C

PowerCap is a registered trademark of Dallas Semiconductor.

PIN CONFIGURATION



LIN DE2CKI	PTION
A0-A18	- Address Input
DQ0-DQ7	- Data Input/Outputs
ĪRQ/FT	- Interrupt, Frequency Test
	Output (Open Drain)
RST	- Power-On Reset Output
	(Open Drain)
$\overline{\text{CE}}$	- Chip Enable
OE	Output Enable

- Output Enable OE WE - Write Enable V_{CC} - Power-Supply Input **GND** - Ground - Crystal Connection X1, X2 - Battery Connection V_{BAT}

Note: Some revisions of this device may incorporate deviations from published specifications known as errata. Multiple revisions of any device may be simultaneously available through various sales channels. For information about device errata, click here: www.maxim-ic.com/errata.

> 1 of 19 RFV: 071305

ORDERING INFORMATION

PART	TEMP RANGE	VOLTAGE (V)	PIN-PACKAGE	TOP MARK**
DS1557P-70	0° C to $+70^{\circ}$ C	5.0	34 PowerCap*	DS1557P-70
DS1557P-70+	0° C to $+70^{\circ}$ C	5.0	34 PowerCap*	DS1557P+70
DS1557P-70IND	-40°C to +85°C	5.0	34 PowerCap*	DS1557P-70
DS1557P-70IND+	-40°C to +85°C	5.0	34 PowerCap*	DS1557P+70
DS1557WP-120	0°C to +70°C	3.3	34 PowerCap*	DS1557WP-120
DS1557WP-120+	0°C to +70°C	3.3	34 PowerCap*	DS1557WP+120
DS1557WP-120IND	-40°C to +85°C	3.3	34 PowerCap*	DS1557WP-120
DS1557WP-120IND+	-40°C to +85°C	3.3	34 PowerCap*	DS1557WP+120

⁺ Denotes a lead-free/RoHS-compliant device.

DESCRIPTION

The DS1557 is a full-function, year-2000-compliant (Y2KC), real-time clock/calendar (RTC) with an RTC alarm, watchdog timer, power-on reset, battery monitor, and 512k x 8 nonvolatile static RAM. User access to all registers within the DS1557 is accomplished with a byte-wide interface as shown in Figure 1. The RTC registers contain century, year, month, date, day, hours, minutes, and seconds data in 24-hour BCD format. Corrections for day of month and leap year are made automatically.

The RTC registers are double-buffered into an internal and external set. The user has direct access to the external set. Clock/calendar updates to the external set of registers can be disabled and enabled to allow the user to access static data. Assuming the internal oscillator is turned on, the internal set of registers is continuously updated; this occurs regardless of external registers settings to guarantee that accurate RTC information is always maintained.

The \overline{IRQ}/FT interrupt (\overline{IRQ}/FT) and reset (\overline{RST}) outputs which can be used to control CPU activity. The \overline{IRQ}/FT interrupt output can be used to generate an external interrupt when the RTC register values match user programmed alarm values. The interrupt is always available while the device is powered from the system supply and can be programmed to occur when in the battery-backed state to serve as a system wakeup. Either the \overline{IRQ}/FT or \overline{RST} outputs can also be used as a CPU watchdog timer, CPU activity is monitored and an interrupt or reset output will be activated if the correct activity is not detected within programmed limits. The DS1557 power-on reset can be used to detect a system power down or failure and hold the CPU in a safe reset state until normal power returns and stabilizes; the \overline{RST} output is used for this function.

The DS1557 also contains its own power-fail circuitry, which automatically deselects the device when the V_{CC} supply enters an out-of-tolerance condition. This feature provides a high degree of data security during unpredictable system operation brought on by low V_{CC} levels.

^{*} DS9034PCX (PowerCap) required. Must be ordered separately.

^{*}An "IND" on the top mark denotes an industrial temperature grade device.

Figure 1. Block Diagram

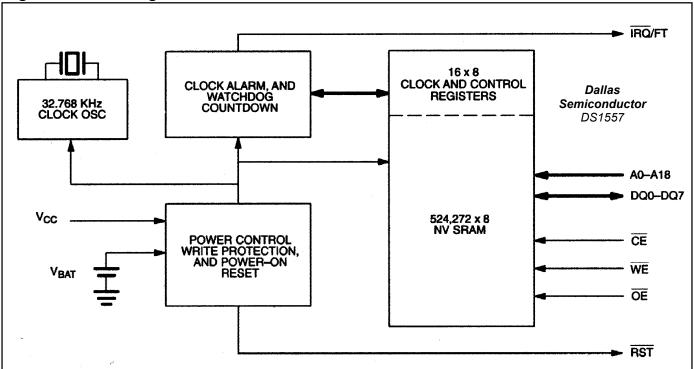


Table 1. Operating Modes

V _{CC}	CE	ŌE	WE	DQ0-DQ7	MODE	POWER
	$V_{ m IH}$	X	X	HIGH-Z	Deselect	Standby
$V_{CC} > V_{PF}$	$V_{ m IL}$	X	$V_{ m IL}$	$\mathrm{D_{IN}}$	Write	Active
V CC > V PF	$V_{ m IL}$	$V_{ m IL}$	V_{IH}	$\mathrm{D}_{\mathrm{OUT}}$	Read	Active
	$V_{\rm IL}$	V_{IH}	V_{IH}	HIGH-Z	Read	Active
$V_{SO} < V_{CC} < V_{PF}$	X	X	X	HIGH-Z	Deselect	CMOS Standby
$V_{CC} < V_{SO} < V_{PF}$	X	X	X	HIGH-Z	Data Retention	Battery Current

DATA READ MODE

The DS1557 is in the read mode whenever \overline{CE} (chip enable) is low and \overline{WE} (write enable) is high. The device architecture allows ripple-through access to any valid address location. Valid data will be available at the DQ pins within t_{AA} after the last address input is stable, providing that \overline{CE} and \overline{OE} access times are satisfied. If \overline{CE} or \overline{OE} access times are not met, valid data will be available at the latter of chip enable access (t_{CEA}) or at output enable access time (t_{OEA}). The state of the data input/output pins (DQ) is controlled by \overline{CE} and \overline{OE} . If the outputs are activated before t_{AA} , the data lines are driven to an intermediate state until t_{AA} . If the address inputs are changed while \overline{CE} and \overline{OE} remain valid, output data will remain valid for output data hold time (t_{OH}) but will then go indeterminate until the next address access.

DATA WRITE MODE

The DS1557 is in the write mode whenever \overline{WE} and \overline{CE} are in their active state. The start of a write is referenced to the latter occurring transition of \overline{WE} or \overline{CE} . The addresses must be held valid throughout the cycle. \overline{CE} and \overline{WE} must return inactive for a minimum of t_{WR} prior to the initiation of a subsequent read or write cycle. Data in must be valid t_{DS} prior to the end of the write and remain valid for t_{DH} afterward. In a typical application, the \overline{OE} signal will be high during a write cycle. However, \overline{OE} can be active provided that care is taken with the data bus to avoid bus contention. If \overline{OE} is low prior to \overline{WE} transitioning low, the data bus can become active with read data defined by the address inputs. A low transition on \overline{WE} will then disable the outputs t_{WEZ} after \overline{WE} goes active.

DATA RETENTION MODE

The 5V device is fully accessible and data can be written and read only when V_{CC} is greater than V_{PF} . However, when V_{CC} is below the power-fail point V_{PF} (point at which write protection occurs) the internal clock registers and SRAM are blocked from any access. When V_{CC} falls below the battery switch point V_{SO} (battery supply level), device power is switched from the V_{CC} pin to the internal backup lithium battery. RTC operation and SRAM data are maintained from the battery until V_{CC} is returned to nominal levels.

The 3.3V device is fully accessible and data can be written and read only when V_{CC} is greater than V_{PF} . When V_{CC} falls below V_{PF} , access to the device is inhibited. If V_{PF} is less than V_{SO} , the device power is switched from V_{CC} to the internal backup lithium battery when V_{CC} drops below V_{PF} . If V_{PF} is greater than V_{SO} , the device power is switched from V_{CC} to the internal backup lithium battery when V_{CC} drops below V_{SO} . RTC operation and SRAM data are maintained from the battery until V_{CC} is returned to nominal levels.

All control, data, and address signals must be powered down when V_{CC} is powered down.

BATTERY LONGEVITY

The DS1557 has a lithium power source that is designed to provide energy for the clock activity, and clock and RAM data retention when the V_{CC} supply is not present. The capability of this internal power supply is sufficient to power the DS1557 continuously for the life of the equipment in which it is installed. For specification purposes, the life expectancy is 10 years at 25°C with the internal clock oscillator running in the absence of V_{CC} .

INTERNAL BATTERY MONITOR

The DS1557 constantly monitors the battery voltage of the internal battery. The Battery Low Flag (BLF) bit of the Flags Register (B4 of 7FFF0h) is not writable and should always be a 0 when read. If a 1 is ever present, an exhausted lithium energy source is indicated and both the contents of the RTC and RAM are questionable.

POWER-ON RESET

A temperature compensated comparator circuit monitors the level of V_{CC} . When V_{CC} falls to the power fail trip point, the \overline{RST} signal (open drain) is pulled low. When V_{CC} returns to nominal levels, the \overline{RST} signal continues to be pulled low for a period of 40 ms to 200 ms. The power-on reset function is independent of the RTC oscillator and thus is operational whether or not the oscillator is enabled.

CLOCK OPERATIONS

Table 2 and the following paragraphs describe the operation of RTC, alarm, and watchdog functions.

Table 2. Register Map

ADDDECC	ADDRESS			DATA	4				ELINCTION/DA	NCE
ADDRESS	B ₇	B ₆	B ₅	\mathbf{B}_4	B ₃	B ₂	\mathbf{B}_1	\mathbf{B}_{0}	FUNCTION/RA	NGL
7FFFFh		10	Year			Year	•		Year	00-99
7FFFEh	X	X	X	10 Month		Mont	h		Month	01-12
7FFFDh	X	X	10 1	Date		Date	;		Date	01-31
7FFFCh	X	FT	X	X	X		Day		Day	01-07
7FFFBh	X	X	10 H	Hour		Hou	r		Hour	00-23
7FFFAh	X		10 Minutes			Minut	es		Minutes	00-59
7FFF9h	OSC		10 Second	ls		Secon	ds		Seconds	00-59
7FFF8h	W	R	10 Ce	entury		Centu	ry		Control	00-39
7FFF7h	WDS	BMB4	Bmb3	BMB2	BMB1	Bmb0	RB1	RB0	Watchdog	
7FFF6h	AE	Y	Abe	Y	Y	Y	Y	Y	Interrupts	
7FFF5h	AM4	Y	10 1	Date		Date			Alarm Date	01-31
7FFF4h	AM3	Y	10 H	Iours		Hour	S		Alarm Hours	00-23
7FFF3h	AM2		10 Minute	es		Minutes			Alarm Minutes	00-59
7FFF2h	AM1		10 Second	ls		Seconds			Alarm Seconds	00-59
7FFF1h	Y	Y	Y	Y	Y Y Y Y		Unused			
7FFF0h	WF	AF	0	BLF	0	0	0	0	Flags	

X = Unused, Read/Writeable Under Write and Read Bit Control

Y = Unused, Read/Writeable Without Write and Read Bit Control

OSC = Oscillator Start/Stop Bit

W = Write Bit

R = Read Bit

WDS = Watchdog Steering Bit

BMB0 to BMB4 = Watchdog Multiplier Bits

RB0 to RB1 = Watchdog Resolution Bits

AE = Alarm Flag Enable

FT = Frequency Test Bit

ABE = Alarm in Battery-BackUp Mode Enable

AM1 to AM4 = Alarm Mask Bits

WF = Watchdog Flag

AF = Alarm Flag

0 = 0 (Read Only)

BLF = Battery Low Flag

CLOCK OSCILLATOR CONTROL

The clock oscillator may be stopped at any time. To increase the shelf life of the backup lithium battery source, the oscillator can be turned off to minimize current drain from the battery. The \overline{OSC} bit is the MSB of the Seconds Register (B7 of 7FFF9h). Setting it to a 1 stops the oscillator, setting to a 0 starts the oscillator. The DS1557 is shipped from Dallas Semiconductor with the clock oscillator turned off, \overline{OSC} bit set to a 1.

READING THE CLOCK

When reading the RTC data, it is recommended to halt updates to the external set of double-buffered RTC Registers. This puts the external registers into a static state allowing data to be read without register values changing during the read process. Normal updates to the internal registers continue while in this state. External updates are halted when a 1 is written into the read bit, B6 of the Control Register (7FFF8h). As long as a 1 remains in the Control Register read bit, updating is halted. After a halt is issued, the registers reflect the RTC count (day, date, and time) that was current at the moment the halt command was issued. Normal updates to the external set of registers will resume within 1 second after the read bit is set to a 0 for a minimum of 500 μ s. The read bit must be a zero for a minimum of 500 μ s to ensure the external registers will be updated.

SETTING THE CLOCK

The MSB bit, B7, of the Control Register is the write bit. Setting the write bit to a 1, like the read bit, halts updates to the DS1557 (7FFF8h-7FFFFh) registers. After setting the write bit to a 1, RTC registers can be loaded with the desired RTC count (day, date, and time) in 24-hour BCD format. Setting the write bit to a 0 then transfers the values written to the internal RTC registers and allows normal operation to resume.

CLOCK ACCURACY

The DS1557 and DS9034PCX are each individually tested for accuracy. Once mounted together, the module will typically keep time accuracy to within ± 1.53 minutes per month (35 ppm) at 25°C and does not require additional calibration. For this reason, methods of field clock calibration are not available and not necessary. The electrical environment also affects clock accuracy and caution should be taken to place the RTC in the lowest-level EMI section of the PC board layout. For additional information, please refer to *Application Note 58*.

FREQUENCY TEST MODE

The DS1557 frequency test mode uses the open drain \overline{IRQ}/FT output. With the oscillator running, the \overline{IRQ}/FT output will toggle at 512 Hz when the FT bit is a 1, the Alarm Flag Enable bit (AE) is a 0, and the Watchdog Steering bit (WDS) is a 1 or the Watchdog Register is reset (Register 7FFF7h = 00h). The \overline{IRQ}/FT output and the frequency test mode can be used as a measure of the actual frequency of the 32.768 kHz RTC oscillator. The \overline{IRQ}/FT pin is an open-drain output that requires a pullup resistor for proper operation. The FT bit is cleared to a 0 on power-up.

USING THE CLOCK ALARM

The alarm settings and control for the DS1557 reside within Registers 7FFF2h-7FFF5h. Register 7FFF6h contains two alarm enable bits: Alarm Enable (AE) and Alarm in Backup Enable (ABE). The AE and ABE bits must be set as described below for the \overline{IRQ}/FT output to be activated for a matched alarm condition.

The alarm can be programmed to activate on a specific day of the month or repeat every day, hour, minute, or second. It can also be programmed to go off while the DS1557 is in the battery-backed state of operation to serve as a system wakeup. Alarm mask bits AM1 to AM4 control the alarm mode. Table 3 shows the possible settings. Configurations not listed in the table default to the once per second mode to notify the user of an incorrect alarm setting.

Table 3. Alarn	n Mask Bits
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AM4	AM3	AM2	AM1	ALARM RATE
1	1	1	1	Once per second
1	1	1	0	When seconds match
1	1	0	0	When minutes and seconds match
1	0	0	0	When hours, minutes, and seconds match
0	0	0	0	When date, hours, minutes, and seconds match

When the RTC Register values match Alarm Register settings, the Alarm Flag bit (AF) is set to a 1. If Alarm Flag Enable (AE) is also set to a 1, the alarm condition activates the \overline{IRQ}/FT pin. The \overline{IRQ}/FT signal is cleared by a read or write to the Flags Register (Address 7FFF0h) as shown in Figure 2 and 3. When \overline{CE} is active, the \overline{IRQ}/FT signal may be cleared by having the address stable for as short as 15 ns and either \overline{OE} or \overline{WE} active, but is not guaranteed to be cleared unless t_{RC} is fulfilled. The alarm flag is also cleared by a read or write to the Flags Register but the flag will not change states until the end of the read/write cycle and the \overline{IRQ}/FT signal has been cleared.

Figure 2. Clearing IRQ Waveforms

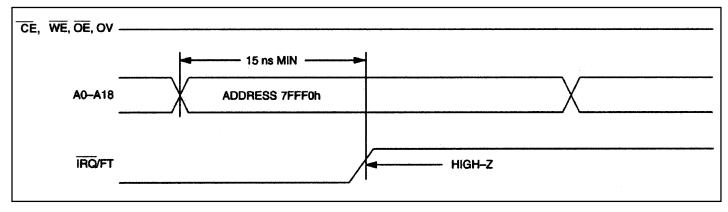
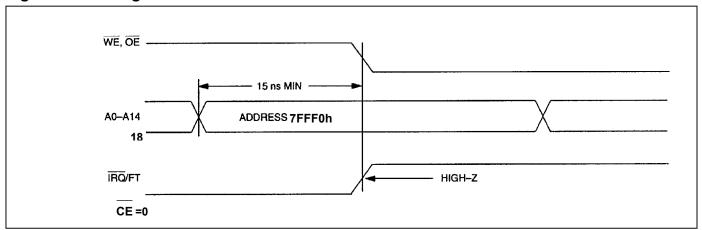
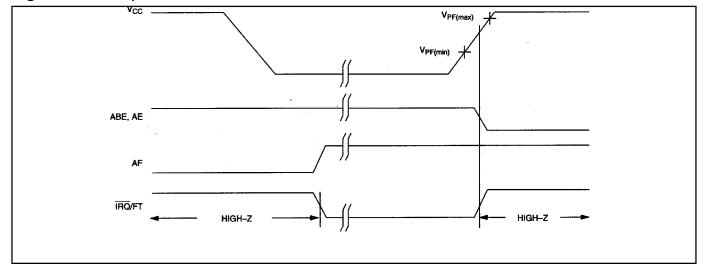


Figure 3. Clearing IRQ Waveforms



The $\overline{\text{IRQ}}/\text{FT}$ pin can also be activated in the battery-backed mode. The $\overline{\text{IRQ}}/\text{FT}$ will go low if an alarm occurs and both ABE and AE are set. The ABE and AE bits are cleared during the power-up transition, however an alarm generated during power-up will set AF. Therefore, the AF bit can be read after system power-up to determine if an alarm was generated during the power-up sequence. Figure 4 illustrates alarm timing during the battery-backup mode and power-up states.

Figure 4. Backup Mode Alarm Waveforms



USING THE WATCHDOG TIMER

The watchdog timer can be used to detect an out-of-control processor. The user programs the watchdog timer by setting the desired amount of timeout into the 8-bit Watchdog Register (Address 7FFF7h). The five Watchdog Register bits BMB4 to BMB0 store a binary multiplier and the two lower order bits RB1 to RB0 select the resolution, where 00=1/16 second, 01=1/4 second, 10=1 second, and 11=4 seconds. The watchdog time-out value is then determined by the multiplication of the 5-bit multiplier value with the 2-bit resolution value. (For example: writing 00001110 in the Watchdog Register = 3 X 1 second or 3 seconds.) If the processor does not reset the timer within the specified period, the Watchdog Flag (WF) is set and a processor interrupt is generated and stays active until either the Watchdog Flag (WF) is read or the Watchdog Register (7FFF7h) is read or written.

The most significant bit of the Watchdog Register is the Watchdog Steering Bit (WDS). When set to a 0, the watchdog will activate the \overline{IRQ} /FT output when the watchdog times out.

When WDS is set to a 1, the watchdog will output a negative pulse on the \overline{RST} output for a duration of 40 ms to 200 ms. The Watchdog Register (7FFF7h) and the FT bit will reset to a 0 at the end of a watchdog timeout when the WDS bit is set to a 1.

The watchdog timer resets when the processor performs a read or write of the Watchdog Register. The timeout period then starts over. Writing a value of 00h to the Watchdog Register disables the watchdog timer. The watchdog function is automatically disabled upon power-up and the Watchdog Register is cleared. If the watchdog function is set to output to the \overline{IRQ}/FT output and the frequency test function is activated, the watchdog function prevails and the frequency test function is denied.

POWER-ON DEFAULT STATES

Upon application of power to the device, the following register bits are set to a 0: WDS = 0, BMB0 to BMB4 = 0, RB0 to RB1 = 0, AE = 0, ABE = 0.

ABSOLUTE MAXIMUM RATINGS

Voltage Range on Any Pin Relative to	Ground	0.3V to +6.0V
Storage Temperature Range		40°C to +85°C
Soldering Temperature	See IPC/JEDEC J-STD-020A	Standard for Surface-Mount Devices (Note 8)

This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

OPERATING RANGE

RANGE	TEMP RANGE	$ m V_{CC}$
Commercial	0°C to +70°C	$3.3V \pm 10\%$ or $5V \pm 10\%$
Industrial	-40°C to +85°C	$3.3V \pm 10\%$ or $5V \pm 10\%$

RECOMMENDED DC OPERATING CONDITIONS

 $(T_A = Over the Operating Range)$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Logic 1 Voltage All Inputs (Note 1)	$V_{ m IH}$	$V_{CC} = 5V \pm 10\%$	2.2		$V_{CC} + 0.3V$	V
	$V_{ m IH}$	$V_{CC} = 3.3V \pm 10\%$	2.0		V _{CC} + 0.3V	V
Logic 0 Voltage All Inputs	$ m V_{IL}$	$V_{CC} = 5V \pm 10\%$	-0.3		+0.8	
(Note 1)	$V_{ m IL}$	$V_{CC} = 3.3V \pm 10\%$	-0.3		+0.6	

DC ELECTRICAL CHARACTERISTICS

 $(V_{CC} = 5.0V \pm 10\%, T_A = Over the Operating Range.)$

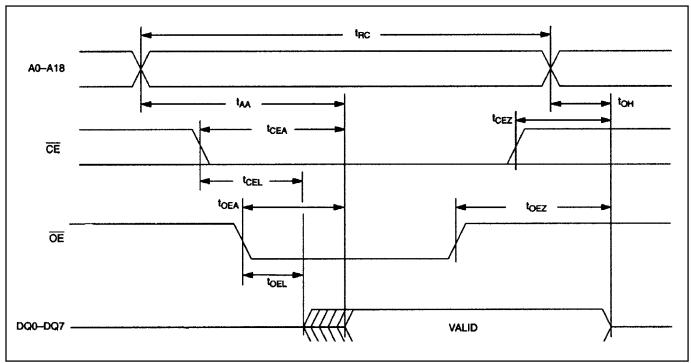
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Active Supply Current	I_{CC}	(Notes 2, 3)		45	90	mA
TTL Standby Current $(\overline{CE} = V_{IH})$	I _{CC1}	(Notes 2, 3)		3	6	mA
CMOS Standby Current $(\overline{CE} \ge V_{CC} - 0.2V)$	I_{CC2}	(Notes 2, 3)		2	6	mA
Input Leakage Current (Any Input)	I_{IL}		-1		+1	μΑ
Output Leakage Current (Any Output)	I_{OL}		-1		+1	μΑ
Output Logic 1 Voltage (I _{OUT} = -1.0 mA)	V_{OH}	(Note 1)	2.4			V
	V_{OL1}	I _{OUT} = 2.1 mA, DQ0–7 Outputs (Note 1)			0.4	V
Output Logic 0 Voltage	V_{OL2}	$I_{OUT} = 7.0 \text{ mA},$ $IRQ/FT, \text{ and } RST$ $Outputs$ $(Notes 1, 5)$			0.4	V
Write Protection Voltage	V_{PF}	(Note 1)	4.20		4.50	V
Battery Switchover Voltage	V_{SO}	(Notes 1, 4)		V_{BAT}		V

DC ELECTRICAL CHARACTERISTICS

 $(V_{cc} = 3.3V \pm 10\%, T_A = Over the Operating Range.)$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Active Supply Current	I_{CC}	(Notes 2, 3)		20	30	mA
TTL Standby Current $(\overline{CE} = V_{IH})$	I_{CC1}	(Notes 2, 3)		2	6	mA
CMOS Standby Current $(\overline{CE} \ge V_{CC} - 0.2V)$	I_{CC2}	(Notes 2, 3)		1	4	mA
Input Leakage Current (Any Input)	$I_{ m IL}$		-1		+1	μΑ
Output Leakage Current (Any Output)	I_{OL}		-1		+1	μΑ
Output Logic 1 Voltage (I _{OUT} = -1.0 mA)	V_{OH}	(Note 1)	2.4			V
	V_{OL1}	I _{OUT} = 2.1 mA, DQ0–7 Outputs (Note 1)			0.4	V
Output Logic 0 Voltage	$ m V_{OL2}$	$I_{OUT} = 7.0 \text{ mA}, \overline{IRQ}/FT$ and \overline{RST} Outputs (Notes 1, 5)			0.4	V
Write Protection Voltage	V_{PF}	(Note 1)	2.75		2.97	V
Battery Switchover Voltage	$ m V_{SO}$	(Notes 1, 4)		$egin{array}{c} V_{BAT} \ or \ V_{PF} \end{array}$		V

Figure 5. Read Cycle Timing Diagram



AC CHARACTERISTICS—READ CYCLE

 $(T_A = Over the Operating Range)$

PARAMETER	SYMBOL	$V_{CC} = 5.0V \pm 10\%$		$V_{\rm CC} = 3.3$	UNITS	
PARAMETER	STRIBOL	MIN	MAX	MIN	MAX	UNIIS
Read Cycle Time	t_{RC}	70		120		ns
Address Access Time	t_{AA}		70		120	ns
CE to DQ Low-Z	$t_{\rm CEL}$	5		5		ns
CE Access Time	t_{CEA}		70		120	ns
CE Data Off Time	t_{CEZ}		25		40	ns
OE to DQ Low-Z	$t_{ m OEL}$	5		5		ns
OE Access Time	$t_{ m OEA}$		35		100	ns
OE Data Off Time	t _{OEZ}		25		35	ns
Output Hold from Address	t_{OH}	5		5		ns

AC CHARACTERISTICS—WRITE CYCLE

 $(T_A = Over the Operating Range)$

PARAMETER	SYMBOL	$V_{CC} = 5.0V \pm 10\%$		$V_{\rm CC} = 3.3 V \pm 10\%$		UNITS
		MIN	MAX	MIN	MAX	UNIIS
Write Cycle Time	t_{WC}	70		120		ns
Address Access Time	t_{AS}	0		0		ns
WE Pulse Width	$t_{ m WEW}$	50		100		ns
CE Pulse Width	t_{CEW}	60		110		ns
Data Setup Time	$t_{ m DS}$	30		80		ns
Data Hold Time (Note 9)	t _{DH1}	5		5		ns
Data Hold Time (Note 10)	t _{DH2}	5		5		ns
Address Hold Time (Note 9)	t _{AH1}	5		0		ns
Address Hold Time (Note 10)	t _{AH2}	5		5		ns
WE Data Off Time	$t_{ m WEZ}$		25		40	ns
Write Recovery Time	$t_{ m WR}$	5		10		ns

Figure 6. Write Cycle Timing, Write-Enable Controlled

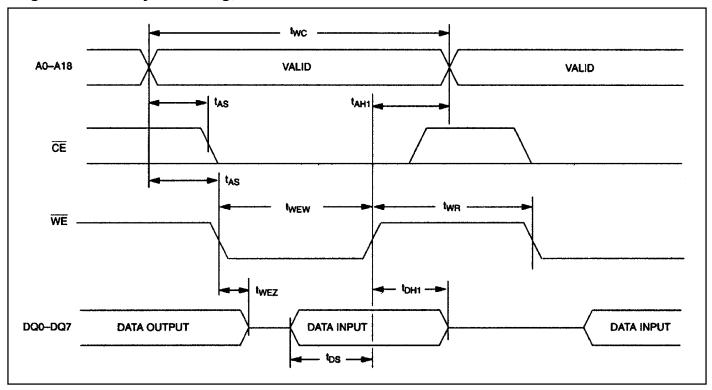
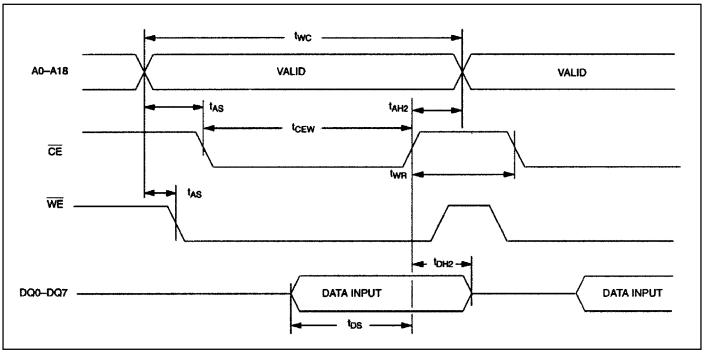


Figure 7. Write Cycle Timing, Chip-Enable Controlled

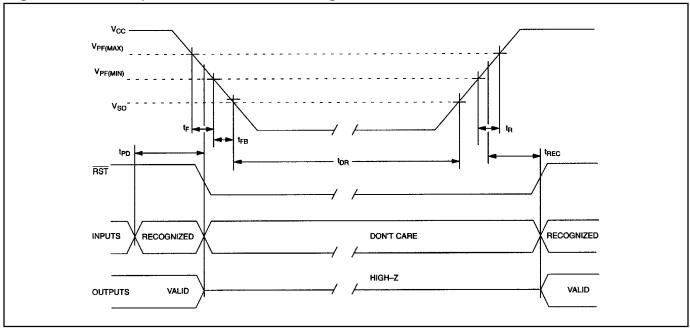


POWER-UP/DOWN CHARACTERISTICS—5V

 $(V_{CC} = 5.0V \pm 10\%, T_A = Over the Operating Range.)$

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
\overline{CE} or \overline{WE} at V_{IH} , Before Power-Down	t_{PD}		0			μs	
V_{CC} Fall Time: $V_{PF(MAX)}$ to $V_{PF(MIN)}$	t_{F}		300			μs	
V_{CC} Fall Time: $V_{\text{PF(MIN)}}$ to V_{SO}	$t_{ m FB}$		10			μs	
V_{CC} Rise Time: $V_{PF(MIN)}$ to $V_{PF(MAX)}$	t_R		0			μs	
V_{PF} to \overline{RST} High	t_{REC}		40		200	ms	
Expected Data-Retention Time (Oscillator On)	$t_{ m DR}$	(Note 6)	10			years	

Figure 8. Power-Up/Down Waveform Timing—5V Device

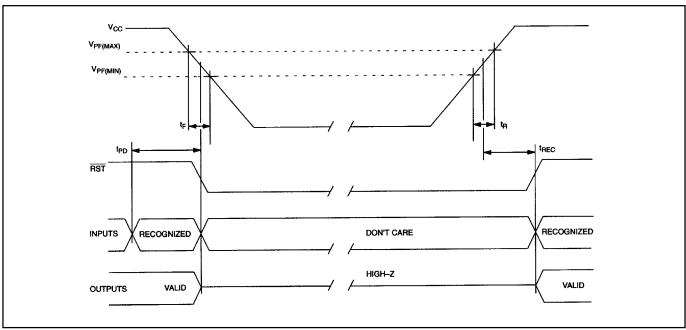


POWER-UP/DOWN CHARACTERISTICS—3.3V

 $(V_{CC} = 3.3V \pm 10\%, T_A = Over the Operating Range.)$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
$\overline{\text{CE}}$ or $\overline{\text{WE}}$ at V_{IH} , Before Power-Down	t_{PD}		0			μs
V_{CC} Fall Time: $V_{PF(MAX)}$ to $V_{PF(MIN)}$	t_{F}		300			μs
V_{CC} Rise Time: $V_{PF(MIN)}$ to $V_{PF(MAX)}$	t_R		0			μs
V _{PF} to RST High	$t_{ m REC}$		40		200	ms
Expected Data-Retention Time (Oscillator On)	$t_{ m DR}$	(Note 6)	10			years

Figure 9. Power-Up/Down Waveform Timing—3.3V Device



CAPACITANCE

 $(T_A = +25^{\circ}C)$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Capacitance on All Input Pins	C_{IN}	(Note 1)			14	pF
Capacitance on \overline{IRQ}/FT , \overline{RST} , and DQ Pins	C _{IO}	(Note 1)			10	pF

AC TEST CONDITIONS

Output Load: 50 pF + 1TTL Gate Input Pulse Levels: 0 to 3.0V

Timing Measurement Reference Levels:

Input: 1.5V Output: 1.5V

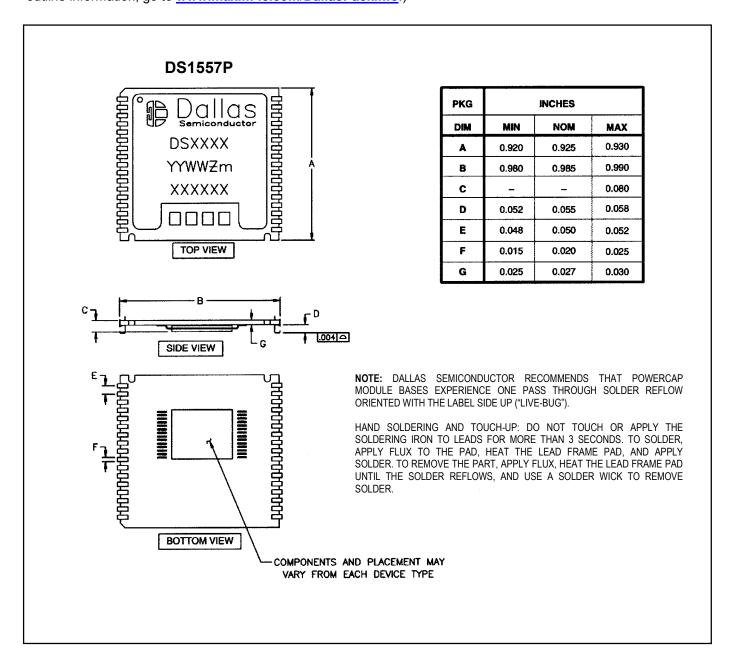
Input Pulse Rise and Fall Times: 5 ns

NOTES:

- 1) Voltage referenced to ground.
- 2) Typical values are at 25°C and nominal supplies.
- 3) Outputs are open.
- 4) Battery switchover occurs at the lower of either the battery voltage or V_{PF}.
- 5) The \overline{IRQ}/FT and \overline{RST} outputs are open drain.
- 6) Data-retention time is at +25°C.
- 7) Dallas Semiconductor recommends that PowerCap Module bases experience one pass through solder reflow oriented with the label side up ("live-bug").
- 8) Hand soldering and touch-up: Do not touch or apply the soldering iron to leads for more than 3 seconds. To solder, apply flux to the pad, heat the lead frame pad, and apply solder. To remove the part, apply flux, heat the lead frame pad until the solder reflow, and use a solder wick to remove solder.
- 9) t_{AH1} , t_{DH1} are measured from \overline{WE} going high.
- 10) t_{AH2} , t_{DH2} are measured from \overline{CE} going high.

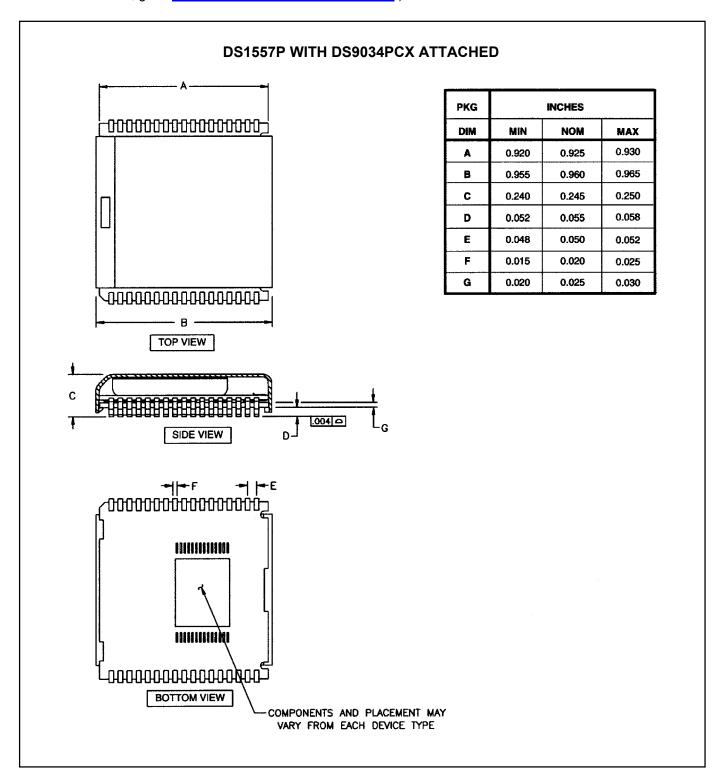
PACKAGE INFORMATION

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/DallasPackInfo.)



PACKAGE INFORMATION (continued)

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PACKAGE INFORMATION (continued)

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